Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, I²C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	123
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 36x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5604bk0vlq6r

1 Introduction

1.1 Document overview

This document describes the features of the family and options available within the family members, and highlights important electrical and physical characteristics of the device. To ensure a complete understanding of the device functionality, refer also to the device reference manual and errata sheet.

1.2 Description

The MPC5604B/C is a family of next generation microcontrollers built on the Power Architecture® embedded category.

The MPC5604B/C family of 32-bit microcontrollers is the latest achievement in integrated automotive application controllers. It belongs to an expanding family of automotive-focused products designed to address the next wave of body electronics applications within the vehicle. The advanced and cost-efficient host processor core of this automotive controller family complies with the Power Architecture embedded category and only implements the VLE (variable-length encoding) APU, providing improved code density. It operates at speeds of up to 64 MHz and offers high performance processing optimized for low power consumption. It capitalizes on the available development infrastructure of current Power Architecture devices and is supported with software drivers, operating systems and configuration code to assist with users implementations.

Table 2. MPC5604B/C device comparison[1]

Feature	Device										
	SPC560B 40L1	**SPC560B 40L3**	**SPC560B 40L5**	**SPC560C 40L1**	**SPC560C 40L3**	**SPC560B 50L1**	**SPC560B 50L3**	**SPC560B 50L5**	**SPC560C 50L1**	**SPC560C 50L3**	**SPC560B 50B2**
CPU	e200z0h										
Execution speed[2]	Static – up to 64 MHz										
Code Flash	256 KB					512 KB					
Data Flash	64 KB (4 × 16 KB)										
RAM	24 KB			32 KB		32 KB			48 KB		
MPU	8-entry										
ADC (10-bit)	12 ch	28 ch	36 ch	8 ch	28 ch	12 ch	28 ch	36 ch	8 ch	28 ch	36 ch
CTU	Yes										
Total timer I/O[3] eMIOS	12 ch, 16-bit	28 ch, 16-bit	56 ch, 16-bit	12 ch, 16-bit	28 ch, 16-bit	12 ch, 16-bit	28 ch, 16-bit	56 ch, 16-bit	12 ch, 16-bit	28 ch, 16-bit	56 ch, 16-bit
• PWM + MC + IC/OC[4]	2 ch	5 ch	10 ch	2 ch	5 ch	2 ch	5 ch	10 ch	2 ch	5 ch	10 ch
• PWM + IC/OC[4]	10 ch	20 ch	40 ch	10 ch	20 ch	10 ch	20 ch	40 ch	10 ch	20 ch	40 ch
• IC/OC[4]	—	3 ch	6 ch	—	3 ch	—	3 ch	6 ch	—	3 ch	6 ch
SCI (LINFlex)	3[5]			4							
SPI (DSPI)	2	3		2	3	2	3		2	3	
CAN (FlexCAN)	2[6]			5	6	3[7]			5	6	
I^2C	1										
32 kHz oscillator	Yes										
GPIO[8]	45	79	123	45	79	45	79	123	45	79	123
Debug	JTAG										Nexus2+
Package	LQFP64[9]	LQFP100	LQFP144	LQFP64[9]	LQFP100	LQFP64[9]	LQFP100	LQFP144	LQFP64[9]	LQFP100	LBGA208[10]

1 Feature set dependent on selected peripheral multiplexing—table shows example implementation

2 Based on 125 °C ambient operating temperature

3 See the eMIOS section of the device reference manual for information on the channel configuration and functions.

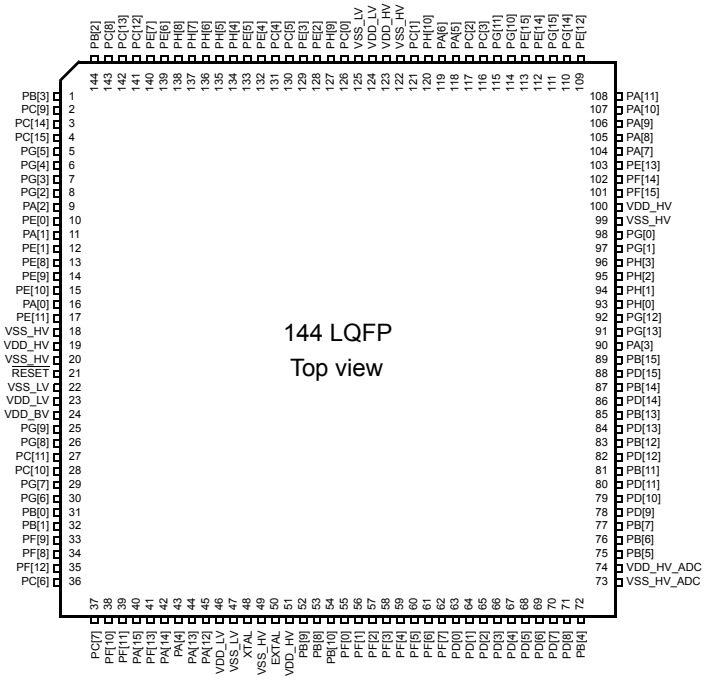
4 IC – Input Capture; OC – Output Compare; PWM – Pulse Width Modulation; MC – Modulus counter

5 SCI0, SCI1 and SCI2 are available. SCI3 is not available.

Table 3 summarizes the functions of all blocks present in the MPC5604B/C series of microcontrollers. Please note that the presence and number of blocks vary by device and package.

Table 3. MPC5604B/C series block summary

Block	Function
Analog-to-digital converter (ADC)	Multi-channel, 10-bit analog-to-digital converter
Boot assist module (BAM)	A block of read-only memory containing VLE code which is executed according to the boot mode of the device
Clock monitor unit (CMU)	Monitors clock source (internal and external) integrity
Cross triggering unit (CTU)	Enables synchronization of ADC conversions with a timer event from the eMIOS or from the PIT
Deserial serial peripheral interface (DSPI)	Provides a synchronous serial interface for communication with external devices
Error Correction Status Module (ECSM)	Provides a myriad of miscellaneous control functions for the device including program-visible information about configuration and revision levels, a reset status register, wakeup control for exiting sleep modes, and optional features such as information on memory errors reported by error-correcting codes
Enhanced Direct Memory Access (eDMA)	Performs complex data transfers with minimal intervention from a host processor via "*n*" programmable channels.
Enhanced modular input output system (eMIOS)	Provides the functionality to generate or measure events
Flash memory	Provides non-volatile storage for program code, constants and variables
FlexCAN (controller area network)	Supports the standard CAN communications protocol
Frequency-modulated phase-locked loop (FMPLL)	Generates high-speed system clocks and supports programmable frequency modulation
Internal multiplexer (IMUX) SIU subblock	Allows flexible mapping of peripheral interface on the different pins of the device
Inter-integrated circuit (I^2C™) bus	A two wire bidirectional serial bus that provides a simple and efficient method of data exchange between devices
Interrupt controller (INTC)	Provides priority-based preemptive scheduling of interrupt requests
JTAG controller	Provides the means to test chip functionality and connectivity while remaining transparent to system logic when not in test mode
LINFlex controller	Manages a high number of LIN (Local Interconnect Network protocol) messages efficiently with a minimum of CPU load
Clock generation module (MC_CGM)	Provides logic and control required for the generation of system and peripheral clocks
Mode entry module (MC_ME)	Provides a mechanism for controlling the device operational mode and mode transition sequences in all functional states; also manages the power control unit, reset generation module and clock generation module, and holds the configuration, control and status registers accessible for applications
Power control unit (MC_PCU)	Reduces the overall power consumption by disconnecting parts of the device from the power supply via a power switching device; device components are grouped into sections called "power domains" which are controlled by the PCU
Reset generation module (MC_RGM)	Centralizes reset sources and manages the device reset sequence of the device



Note:
Availability of port pin alternate functions depends on product selection.

Figure 5. LQFP 144-pin configuration

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number				
								MPC560xB 64 LQFP	MPC560xC 64 LQFP	100 LQFP	144 LQFP	208 MAPBGA[3]
PB[10]	PCR[26]	AF0 AF1 AF2 AF3 — —	GPIO[26] — — — ANS[2] WKPU[8][4]	SIUL — — — ADC WKPU	I/O — — — I I	J	Tristate	31	31	40	54	P9
PB[11][8]	PCR[27]	AF0 AF1 AF2 AF3 —	GPIO[27] E0UC[3] — CS0_0 ANS[3]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — I/O I	J	Tristate	38	36	59	81	N13
PB[12]	PCR[28]	AF0 AF1 AF2 AF3 —	GPIO[28] E0UC[4] — CS1_0 ANX[0]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	39	—	61	83	M16
PB[13]	PCR[29]	AF0 AF1 AF2 AF3 —	GPIO[29] E0UC[5] — CS2_0 ANX[1]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	40	—	63	85	M13
PB[14]	PCR[30]	AF0 AF1 AF2 AF3 —	GPIO[30] E0UC[6] — CS3_0 ANX[2]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	41	37	65	87	L16
PB[15]	PCR[31]	AF0 AF1 AF2 AF3 —	GPIO[31] E0UC[7] — CS4_0 ANX[3]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	42	38	67	89	L13
PC[0][9]	PCR[32]	AF0 AF1 AF2 AF3	GPIO[32] — TDI —	SIUL — JTAGC —	I/O — I —	M	Input, weak pull-up	59	59	87	126	A8
PC[1][9]	PCR[33]	AF0 AF1 AF2 AF3	GPIO[33] — TDO[10] —	SIUL — JTAGC —	I/O — O —	M	Tristate	54	54	82	121	C9

[2] C_L includes device and package capacitances (C_{PKG} < 5 pF).

3.15.5 I/O pad current specification

The I/O pads are distributed across the I/O supply segment. Each I/O supply segment is associated to a V_{DD}/V_{SS} supply pair as described in Table 22.

Table 22. I/O supply segment

Package	Supply segment					
	1	2	3	4	5	6
208 MAPBGA[1]	Equivalent to 144 LQFP segment pad distribution				MCKO	MDOn/MSEO
144 LQFP	pin20–pin49	pin51–pin99	pin100–pin122	pin 123–pin19	—	—
100 LQFP	pin16–pin35	pin37–pin69	pin70–pin83	pin 84–pin15	—	—
64 LQFP	pin8–pin26	pin28–pin55	pin56–pin7	—	—	—

[1] 208 MAPBGA available only as development package for Nexus2+

Table 23 provides I/O consumption figures.

In order to ensure device reliability, the average current of the I/O on a single segment should remain below the I_{AVGSEG} maximum value.

Table 23. I/O consumption

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
I_{SWTSLW}[2]	CC	D	Dynamic I/O current for SLOW configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	20	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	16	
I_{SWTMED}[2]	CC	D	Dynamic I/O current for MEDIUM configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	29	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	17	
I_{SWTFST}[2]	CC	D	Dynamic I/O current for FAST configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	110	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	50	
I_{RMSSLW}	CC	D	Root mean square I/O current for SLOW configuration	C_L = 25 pF, 2 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	2.3	mA
				C_L = 25 pF, 4 MHz		—	—	3.2	
				C_L = 100 pF, 2 MHz		—	—	6.6	
				C_L = 25 pF, 2 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	1.6	
				C_L = 25 pF, 4 MHz		—	—	2.3	
				C_L = 100 pF, 2 MHz		—	—	4.7	

Table 24. I/O weight[1] (continued)

Supply segment			Pad	144/100 LQFP				64 LQFP			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
144 LQFP	100 LQFP	64 LQFP[2]		SRC[3] = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
4	—	—	PG[2]	8%	12%	10%	10%	—	—	—	—
	4	3	PA[2]	8%	—	9%	—	8%	—	9%	—
		—	PE[0]	8%	—	9%	—	—	—	—	—
		3	PA[1]	7%	—	9%	—	7%	—	9%	—
		—	PE[1]	7%	10%	8%	9%	—	—	—	—
		—	PE[8]	7%	9%	8%	8%	—	—	—	—
		—	PE[9]	6%	—	7%	—	—	—	—	—
		—	PE[10]	6%	—	7%	—	—	—	—	—
		3	PA[0]	5%	8%	6%	7%	5%	8%	6%	7%
		—	PE[11]	5%	—	6%	—	—	—	—	—
1	—	—	PG[9]	9%	—	10%	—	—	—	—	—
	—	—	PG[8]	9%	—	11%	—	—	—	—	—
	1	—	PC[11]	9%	—	11%	—	—	—	—	—
		1	PC[10]	9%	13%	11%	12%	9%	13%	11%	12%
	—	—	PG[7]	10%	14%	11%	12%	—	—	—	—
	—	—	PG[6]	10%	14%	12%	12%	—	—	—	—
	1	1	PB[0]	10%	14%	12%	12%	10%	14%	12%	12%
			PB[1]	10%	—	12%	—	10%	—	12%	—
	—	—	PF[9]	10%	—	12%	—	—	—	—	—
	—	—	PF[8]	10%	15%	12%	13%	—	—	—	—
	—	—	PF[12]	10%	15%	12%	13%	—	—	—	—
	1	1	PC[6]	10%	—	12%	—	10%	—	12%	—
			PC[7]	10%	—	12%	—	10%	—	12%	—
	—	—	PF[10]	10%	14%	12%	12%	—	—	—	—
	—	—	PF[11]	10%	—	11%	—	—	—	—	—
	1	1	PA[15]	9%	12%	10%	11%	9%	12%	10%	11%
	—	—	PF[13]	8%	—	10%	—	—	—	—	—
	1	1	PA[14]	8%	11%	9%	10%	8%	11%	9%	10%
			PA[4]	8%	—	9%	—	8%	—	9%	—
			PA[13]	7%	10%	9%	9%	7%	10%	9%	9%
			PA[12]	7%	—	8%	—	7%	—	8%	—

Table 24. I/O weight[1] (continued)

Supply segment			Pad	144/100 LQFP				64 LQFP			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
144 LQFP	100 LQFP	64 LQFP[2]		SRC[3] = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
2	2	2	PB[9]	1%	—	1%	—	1%	—	1%	—
			PB[8]	1%	—	1%	—	1%	—	1%	—
			PB[10]	6%	—	7%	—	6%	—	7%	—
	—	—	PF[0]	6%	—	7%	—	—	—	—	—
	—	—	PF[1]	7%	—	8%	—	—	—	—	—
	—	—	PF[2]	7%	—	8%	—	—	—	—	—
	—	—	PF[3]	7%	—	9%	—	—	—	—	—
	—	—	PF[4]	8%	—	9%	—	—	—	—	—
	—	—	PF[5]	8%	—	10%	—	—	—	—	—
	—	—	PF[6]	8%	—	10%	—	—	—	—	—
	—	—	PF[7]	9%	—	10%	—	—	—	—	—
	2	—	PD[0]	1%	—	1%	—	—	—	—	—
		—	PD[1]	1%	—	1%	—	—	—	—	—
		—	PD[2]	1%	—	1%	—	—	—	—	—
		—	PD[3]	1%	—	1%	—	—	—	—	—
		—	PD[4]	1%	—	1%	—	—	—	—	—
		—	PD[5]	1%	—	1%	—	—	—	—	—
		—	PD[6]	1%	—	1%	—	—	—	—	—
		—	PD[7]	1%	—	1%	—	—	—	—	—
		—	PD[8]	1%	—	1%	—	—	—	—	—
		2	PB[4]	1%	—	1%	—	1%	—	1%	—
			PB[5]	1%	—	1%	—	1%	—	2%	—
			PB[6]	1%	—	1%	—	1%	—	2%	—
			PB[7]	1%	—	1%	—	1%	—	2%	—
		—	PD[9]	1%	—	1%	—	—	—	—	—
		—	PD[10]	1%	—	1%	—	—	—	—	—
		—	PD[11]	1%	—	1%	—	—	—	—	—
		2	PB[11]	11%	—	13%	—	17%	—	21%	—
		—	PD[12]	11%	—	13%	—	—	—	—	—
		2	PB[12]	11%	—	13%	—	18%	—	21%	—
		—	PD[13]	10%	—	12%	—	—	—	—	—

Therefore it is recommended that the user apply EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

- Software recommendations: The software flowchart must include the management of runaway conditions such as:
  - Corrupted program counter
  - Unexpected reset
  - Critical data corruption (control registers...)
- Prequalification trials: Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the reset pin or the oscillator pins for 1 second.

  To complete these trials, ESD stress can be applied directly on the device. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring.

3.20.2 Electromagnetic interference (EMI)

The product is monitored in terms of emission based on a typical application. This emission test conforms to the IEC 61967-1 standard, which specifies the general conditions for EMI measurements.

Table 34. EMI radiated emission measurement[1,2]

Symbol		C	Parameter	Conditions		Value			Unit
						Min	Typ	Max	
—	SR	—	Scan range	—		0.150	—	1000	MHz
f_{CPU}	SR	—	Operating frequency	—		—	64	—	MHz
V_{DD_LV}	SR	—	LV operating voltages	—		—	1.28	—	V
S_{EMI}	CC	T	Peak level	V_{DD} = 5 V, T_A = 25 °C, LQFP144 package Test conforming to IEC 61967-2, f_{OSC} = 8 MHz/f_{CPU} = 64 MHz	No PLL frequency modulation	—	—	18	dBµV
					±2% PLL frequency modulation	—	—	14	dBµV

1 EMI testing and I/O port waveforms per IEC 61967-1, -2, -4

2 For information on conducted emission and susceptibility measurement (norm IEC 61967-4), please contact your local marketing representative.

3.20.3 Absolute maximum ratings (electrical sensitivity)

Based on two different tests (ESD and LU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity.

3.20.3.1 Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). This test conforms to the AEC-Q100-002/-003/-011 standard.

3.26.3 ADC electrical characteristics

Table 44. ADC input leakage current

Symbol		C	Parameter	Conditions		Value			Unit
						Min	Typ	Max	
I_{LKG}	CC	D	Input leakage current	T_A = –40 °C	No current injection on adjacent pin	—	1	70	nA
		D		T_A = 25 °C		—	1	70	
		D		T_A = 85 °C		—	3	100	
		D		T_A = 105 °C		—	8	200	
		P		T_A = 125 °C		—	45	400	

Table 45. ADC conversion characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
V_{SS_ADC}	SR	—	Voltage on VSS_HV_ADC (ADC reference) pin with respect to ground (V_{SS})[2]	—	–0.1	—	0.1	V
V_{DD_ADC}	SR	—	Voltage on VDD_HV_ADC pin (ADC reference) with respect to ground (V_{SS})	—	V_{DD}–0.1	—	V_{DD}+0.1	V
V_{AINx}	SR	—	Analog input voltage[3]	—	V_{SS_ADC}–0.1	—	V_{DD_ADC}+0.1	V
f_{ADC}	SR	—	ADC analog frequency	—	6	—	32 + 4%	MHz
Δ_{ADC_SYS}	SR	—	ADC digital clock duty cycle (ipg_clk)	ADCLKSEL = 1[4]	45	—	55	%
I_{ADCPWD}	SR	—	ADC0 consumption in power down mode	—	—	—	50	µA
I_{ADCRUN}	SR	—	ADC0 consumption in running mode	—	—	—	4	mA
t_{ADC_PU}	SR	—	ADC power up delay	—	—	—	1.5	µs
t_s	CC	T	Sampling time[5]	f_{ADC} = 32 MHz, INPSAMP = 17	0.5	—		µs
				f_{ADC} = 6 MHz, INPSAMP = 255	—	—	42	
t_c	CC	P	Conversion time[6]	f_{ADC} = 32 MHz, INPCMP = 2	0.625	—		µs
C_S	CC	D	ADC input sampling capacitance	—	—	—	3	pF
C_{P1}	CC	D	ADC input pin capacitance 1	—	—	—	3	pF
C_{P2}	CC	D	ADC input pin capacitance 2	—	—	—	1	pF

Table 45. ADC conversion characteristics (continued)

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
C_{P3}	CC	D	ADC input pin capacitance 3	—		—	—	1	pF
R_{SW1}	CC	D	Internal resistance of analog source	—		—	—	3	kΩ
R_{SW2}	CC	D	Internal resistance of analog source	—		—	—	2	kΩ
R_{AD}	CC	D	Internal resistance of analog source	—		—	—	2	kΩ
I_{INJ}	SR	—	Input current Injection	Current injection on one ADC input, different from the converted one	V_{DD} = 3.3 V ± 10%	–5	—	5	mA
					V_{DD} = 5.0 V ± 10%	–5	—	5	
| INL |	CC	T	Absolute value for integral non-linearity	No overload		—	0.5	1.5	LSB
| DNL |	CC	T	Absolute differential non-linearity	No overload		—	0.5	1.0	LSB
$\| E_O \|$	CC	T	Absolute offset error	—		—	0.5	—	LSB
$\| E_G \|$	CC	T	Absolute gain error	—		—	0.6	—	LSB
TUEp	CC	P	Total unadjusted error[7] for precise channels, input only pins	Without current injection		–2	0.6	2	LSB
		T		With current injection		–3		3	
TUEx	CC	T	Total unadjusted error[7] for extended channel	Without current injection		–3	1	3	LSB
		T		With current injection		–4		4	

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.

2 Analog and digital V_{SS} **must** be common (to be tied together externally).

3 V_{AINx} may exceed V_{SS_ADC} and V_{DD_ADC} limits, remaining on absolute maximum ratings, but the results of the conversion will be clamped respectively to 0x000 or 0x3FF.

4 Duty cycle is ensured by using system clock without prescaling. When ADCLKSEL = 0, the duty cycle is ensured by internal divider by 2.

5 During the sampling time the input capacitance C_S can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_s. After the end of the sampling time t_s, changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_s depend on programming.

6 This parameter does not include the sampling time t_s, but only the time for determining the digital result and the time to load the result's register with the conversion result.

7 Total Unadjusted Error: The maximum error that occurs without adjusting Offset and Gain errors. This error is a combination of Offset, Gain and Integral Linearity errors.

3.27 On-chip peripherals

3.27.1 Current consumption

Table 46. On-chip peripherals current consumption[1]

Symbol		C	Parameter	Conditions		Typical value[2]	Unit
$I_{DD\_BV(CAN)}$	CC	T	CAN (FlexCAN) supply current on VDD_BV	Bitrate: 500 Kbyte/s	Total (static + dynamic) consumption: • FlexCAN in loop-back mode • XTAL @ 8 MHz used as CAN engine clock source • Message sending period is 580 µs	8 * f_{periph} + 85	µA
				Bitrate: 125 Kbyte/s		8 * f_{periph} + 27	
$I_{DD\_BV(eMIOS)}$	CC	T	eMIOS supply current on VDD_BV	Static consumption: • eMIOS channel OFF • Global prescaler enabled		29 * f_{periph}	µA
				Dynamic consumption: • It does not change varying the frequency (0.003 mA)		3	
$I_{DD\_BV(SCI)}$	CC	T	SCI (LINFlex) supply current on VDD_BV	Total (static + dynamic) consumption: • LIN mode • Baudrate: 20 Kbyte/s		5 * f_{periph} + 31	µA
$I_{DD\_BV(SPI)}$	CC	T	SPI (DSPI) supply current on VDD_BV	Ballast static consumption (only clocked)		1	µA
				Ballast dynamic consumption (continuous communication): • Baudrate: 2 Mbit/s • Transmission every 8 µs • Frame: 16 bits		16 * f_{periph}	
$I_{DD\_BV(ADC)}$	CC	T	ADC supply current on VDD_BV	V_{DD} = 5.5 V	Ballast static consumption (no conversion)	41 * f_{periph}	µA
					Ballast dynamic consumption (continuous conversion)[3]	5 * f_{periph}	
$I_{DD\_HV\_ADC(ADC)}$	CC	T	ADC supply current on VDD_HV_ADC	V_{DD} = 5.5 V	Analog static consumption (no conversion)	2 * f_{periph}	µA
					Analog dynamic consumption (continuous conversion)	75 * f_{periph} + 32	
$I_{DD\_HV(FLASH)}$	CC	T	Code Flash + Data Flash supply current on VDD_HV	V_{DD} = 5.5 V	—	8.21	mA
$I_{DD\_HV(PLL)}$	CC	T	PLL supply current on VDD_HV	V_{DD} = 5.5 V	—	30 * f_{periph}	µA

1 Operating conditions: T_A = 25 °C, f_{periph} = 8 MHz to 64 MHz

2 f_{periph} is an absolute value.

Table 47. DSPI characteristics[1] (continued)

No.	Symbol		C	Parameter		DSPI0/DSPI1			DSPI2			Unit
						Min	Typ	Max	Min	Typ	Max	
10	t_{HI}	SR	D	Data hold time for inputs	Master mode	0	—	—	0	—	—	ns
					Slave mode	2^6	—	—	2^6	—	—	
11	t_{SUO}[7]	CC	D	Data valid after SCK edge	Master mode	—	—	32	—	—	50	ns
					Slave mode	—	—	52	—	—	160	
12	t_{HO}[7]	CC	D	Data hold time for outputs	Master mode	0	—	—	0	—	—	ns
					Slave mode	8	—	—	13	—	—	

1 Operating conditions: C_L = 10 to 50 pF, $Slew_{IN}$ = 3.5 to 15 ns.

2 Maximum value is reached when CSn pad is configured as SLOW pad while SCK pad is configured as MEDIUM. A positive value means that SCK starts before CSn is asserted. DSPI2 has only SLOW SCK available.

3 Maximum value is reached when CSn pad is configured as MEDIUM pad while SCK pad is configured as SLOW. A positive value means that CSn is deasserted before SCK. DSPI0 and DSPI1 have only MEDIUM SCK available.

4 The t_{CSC} delay value is configurable through a register. When configuring t_{CSC} (using PCSSCK and CSSCK fields in DSPI_CTARx registers), delay between internal CS and internal SCK must be higher than Δt_{CSC} to ensure positive t_{CSCext}.

5 The t_{ASC} delay value is configurable through a register. When configuring t_{ASC} (using PASC and ASC fields in DSPI_CTARx registers), delay between internal CS and internal SCK must be higher than Δt_{ASC} to ensure positive t_{ASCext}.

6 This delay value corresponds to SMPL_PT = 00b which is bit field 9 and 8 of the DSPI_MCR.

7 SCK and SOUT configured as MEDIUM pad

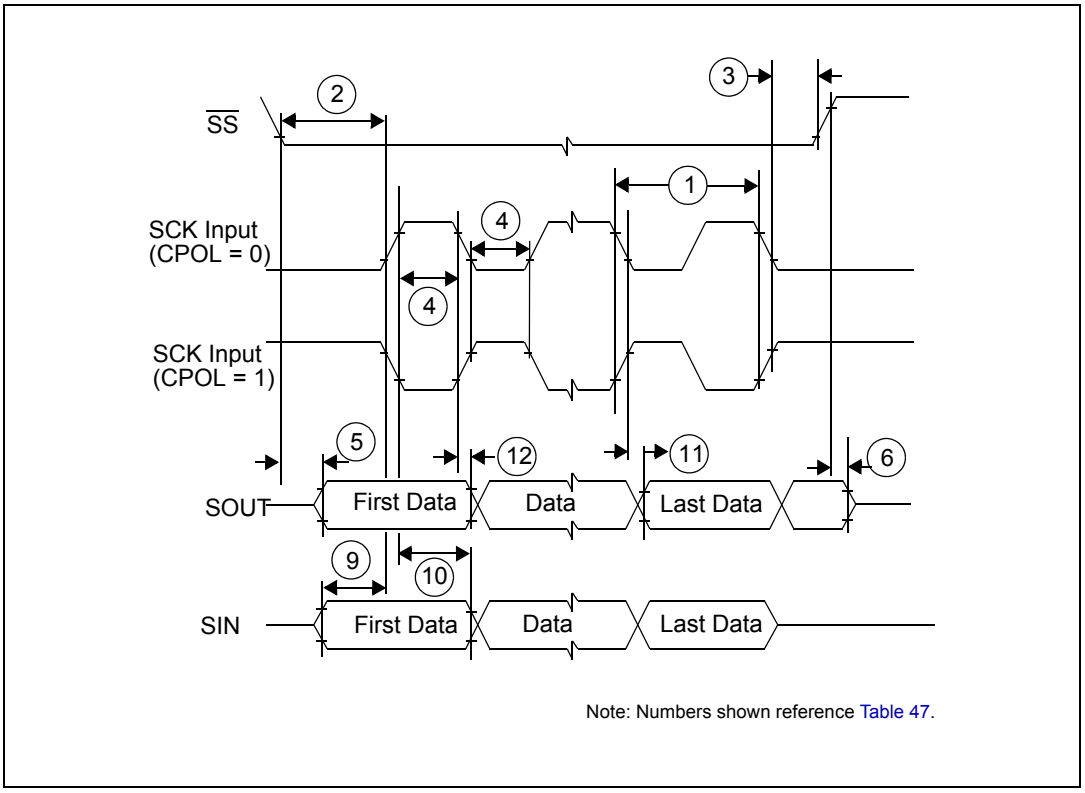


Figure 26. DSPI classic SPI timing – slave, CPHA = 0

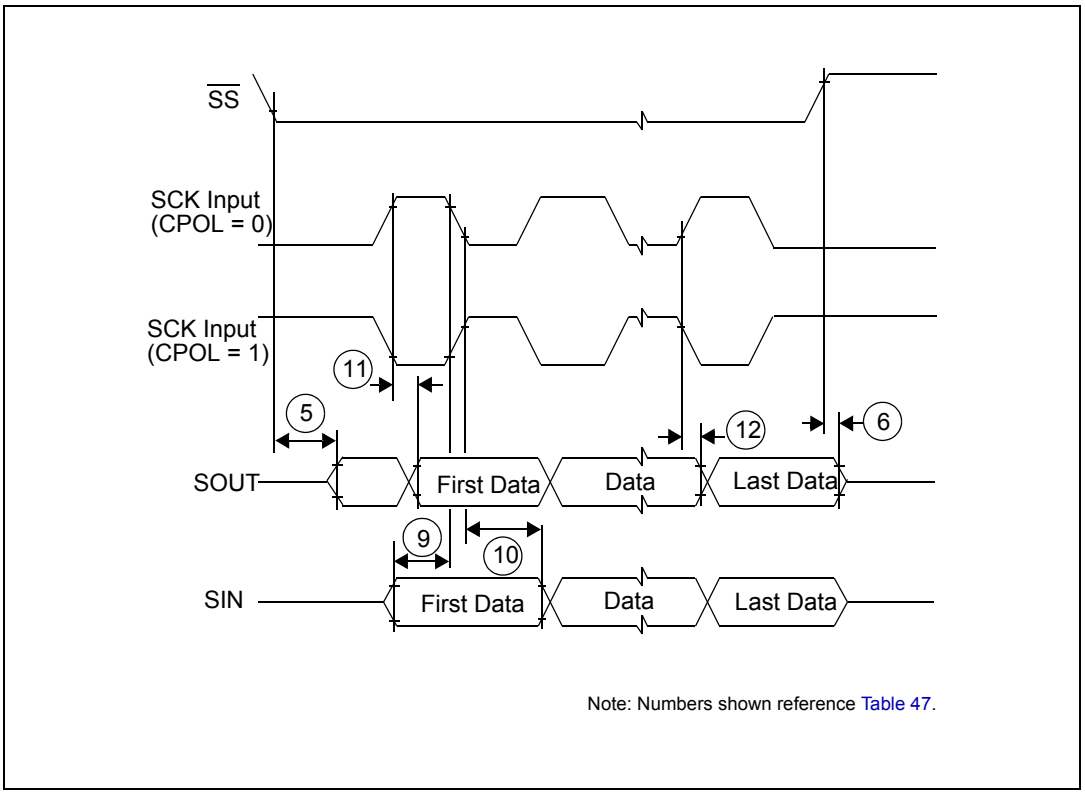


Figure 27. DSPI classic SPI timing – slave, CPHA = 1

4.1.1 64 LQFP

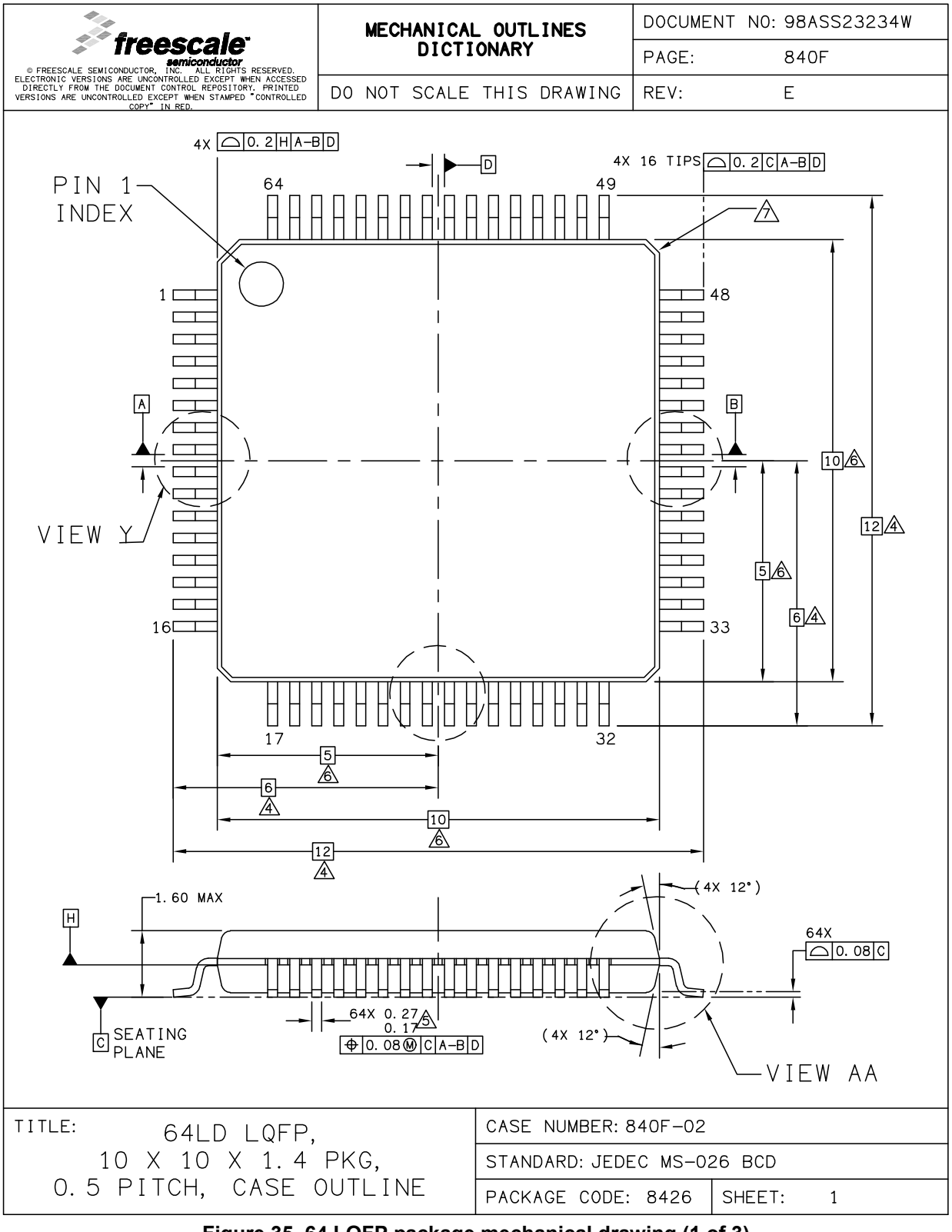


Figure 35. 64 LQFP package mechanical drawing (1 of 3)

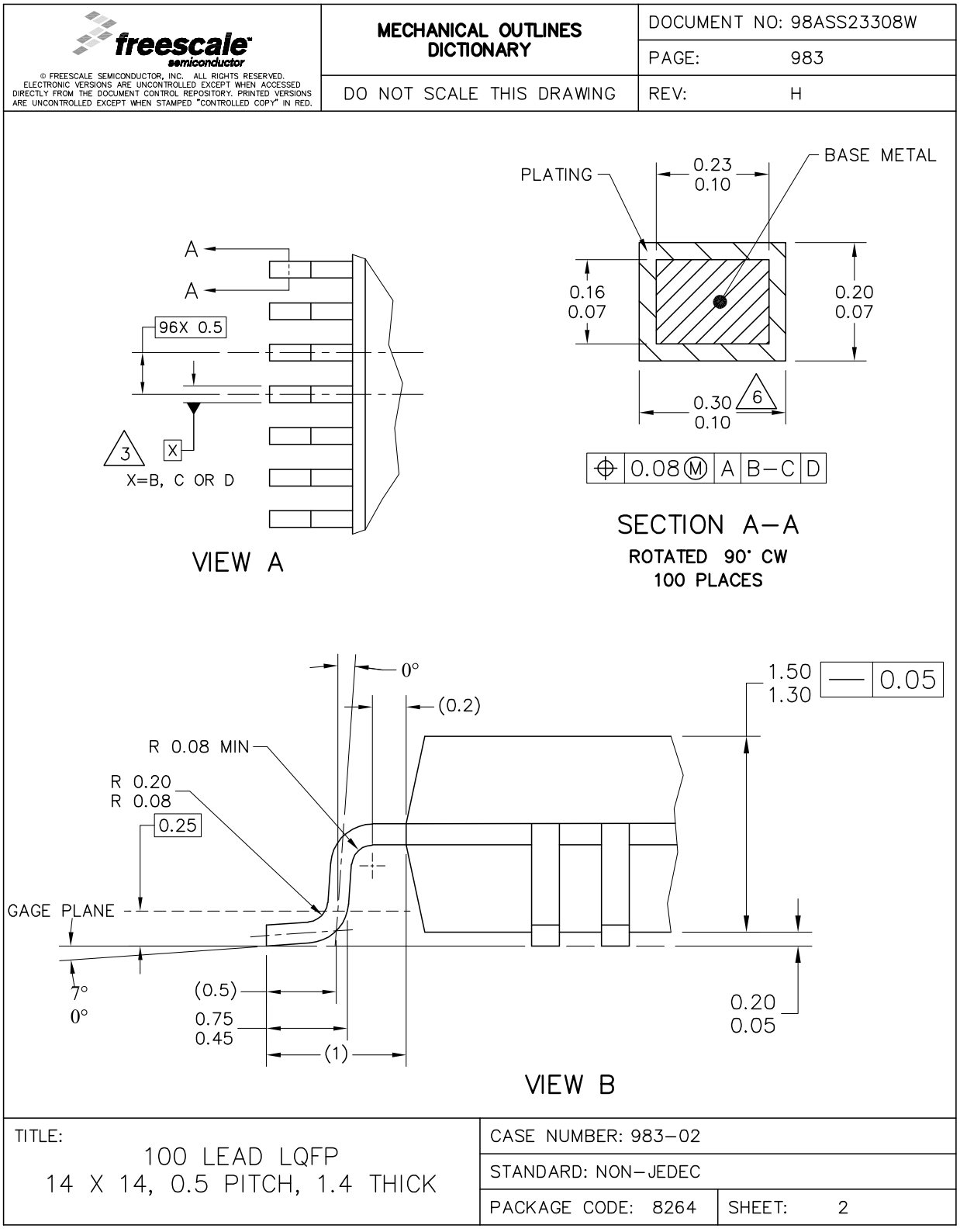


Figure 39. 100 LQFP package mechanical drawing (2 of 3)

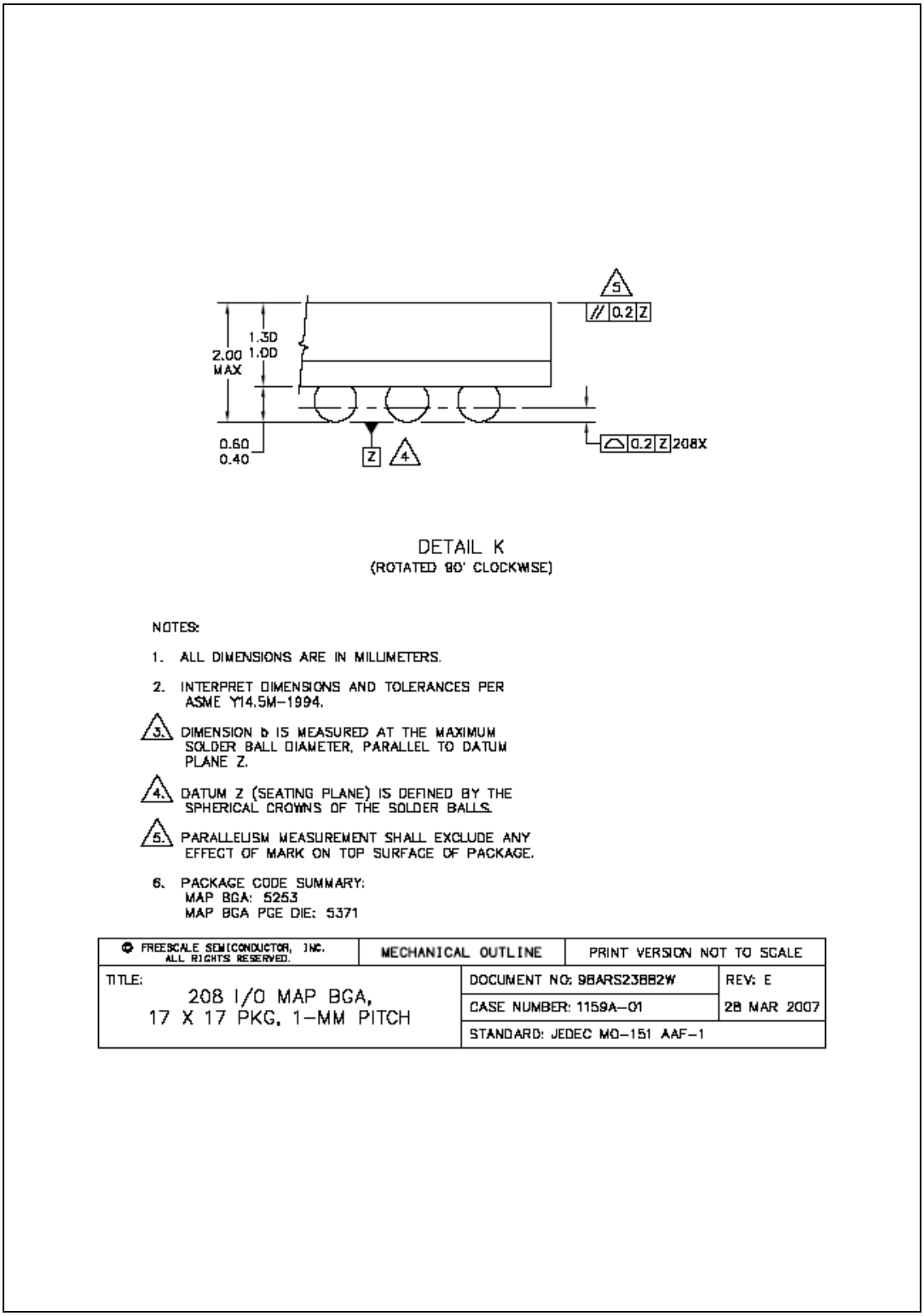


Figure 44. 208 MAPBGA package mechanical drawing (2 of 2)

Table 50. Revision history (continued)

Revision	Date	Description of Changes
2	06-Mar-2009	Made minor editing and formatting changes to improve readability Harmonized oscillator naming throughout document Features: —Replaced 32 KB with 48 KB as max SRAM size —Updated description of INTC —Changed max number of GPIO pins from 121 to 123 Updated Section 1.2, Description Updated Table 2 Added Section 2, Block diagram Section 3, Package pinouts and signal descriptions: Removed signal descriptions (these are found in the device reference manual) Updated Figure 5: —Replaced VPP with VSS_HV on pin 18 —Added MA[1] as AF3 for PC[10] (pin 28) —Added MA[0] as AF2 for PC[3] (pin 116) —Changed description for pin 120 to PH[10] / GPIO[122] / TMS —Changed description for pin 127 to PH[9] / GPIO[121] / TCK —Replaced NMI[0] with NMI on pin 11 Updated Figure 4: —Replaced VPP with VSS_HV on pin 14 —Added MA[1] as AF3 for PC[10] (pin 22) —Added MA[0] as AF2 for PC[3] (pin 77) —Changed description for pin 81 to PH[10] / GPIO[122] / TMS —Changed description for pin 88 to PH[9] / GPIO[121] / TCK —Removed E1UC[19] from pin 76 —Replaced [11] with WKUP[11] for PB[3] (pin 1) —Replaced NMI[0] with NMI on pin 7 Updated Figure 6: —Changed description for ball B8 from TCK to PH[9] —Changed description for ball B9 from TMS to PH[10] —Updated descriptions for balls R9 and T9 Added Section 3.10, Parameter classification and tagged parameters in tables where appropriate Added Section 3.11, NVUSRO register Updated Table 12 Section 3.13, Recommended operating conditions: Added note on RAM data retention to end of section Updated Table 13 and Table 14 Added Section 3.14.1, Package thermal characteristics Updated Section 3.14.2, Power considerations Updated Figure 7

Table 50. Revision history (continued)

Revision	Date	Description of Changes
2 (cont.)	06-Mar-2009	Updated Table 16, Table 17, Table 18, Table 19 and Table 20 Added Section 3.15.4, Output pin transition times Updated Table 23 Updated Figure 8 Updated Table 25 Section 3.17.1, Voltage regulator electrical characteristics: Amended description of LV_PLL Figure 10: Exchanged position of symbols C_{DEC1} and C_{DEC2} Updated Table 26 Added Figure 13 Updated Table 27 and Table 28 Updated Section 3.19, Flash memory electrical characteristics Added Section 3.20, Electromagnetic compatibility (EMC) characteristics Updated Section 3.21, Fast external crystal oscillator (4 to 16 MHz) electrical characteristics Updated Section 3.22, Slow external crystal oscillator (32 kHz) electrical characteristics Updated Table 41, Table 42 and Table 43 Added Section 3.27, On-chip peripherals Added Table 44 Updated Table 45 Updated Table 47 Added Section Appendix A, Abbreviations

Table 50. Revision history (continued)

Revision	Date	Description of Changes
10	15 Oct 2012	Table 1 (MPC5604B/C device comparison), added footnote for MPC5603BxLH and MPC5604BxLH about FlexCAN availability. Table 3 (MPC5604B/C series block summary), replaced “System watchdog timer” with “Software watchdog timer” and specified AUTOSAR (Automotive Open System Architecture) Table 6 (Functional port pin descriptions): replaced footnote “Available only on MPC560xC versions and MPC5604B 208 MAPBGA devices” with “Available only on MPC560xC versions, MPC5603B 64 LQFP, MPC5604B 64 LQFP and MPC5604B 208 MAPBGA devices”, replaced VDD with VDD_HV Figure 10 (Voltage regulator capacitance connection), updated pin name apperence Renamed Figure 11 (V_{DD_HV} and V_{DD_BV} maximum slope) (was “VDD and VDD_BV maximum slope”) Renamed Figure 12 (V_{DD_HV} and V_{DD_BV} supply constraints during STANDBY mode exit) (was “VDD and VDD_BV supply constraints during STANDBY mode exit”) Table 13 (Recommended operating conditions (3.3 V)), added minimum value of T_{VDD} and footnote about it. Table 14 (Recommended operating conditions (5.0 V)), added minimum value of T_{VDD} and footnote about it. Section 3.17.1, “Voltage regulator electrical characteristics: replaced “slew rate of V_{DD}/V_{DD_BV}” with “slew rate of both V_{DD_HV} and V_{DD_BV}” replaced “When STANDBY mode is used, further constraints apply to the V_{DD}/V_{DD_BV} in order to guarantee correct regulator functionality during STANDBY exit.” with “When STANDBY mode is used, further constraints are applied to the both V_{DD_HV} and V_{DD_BV} in order to guarantee correct regulator function during STANDBY exit.” Table 28 (Power consumption on VDD_BV and VDD_HV), updated footnotes of I_{DDMAX} and I_{DDRUN} stating that both currents are drawn only from the V_{DD_BV} pin. Table 32 (Flash memory power supply DC electrical characteristics), in the paremeter column replaced V_{DD_BV} and V_{DD_HV} respectively with VDD_BV and VDD_HV. Table 46 (On-chip peripherals current consumption), in the paremeter column replaced V_{DD_BV}, V_{DD_HV} and $V_{DD\_HV\_ADC}$ respectively with VDD_BV, VDD_HV and VDD_HV_ADC Updated Section 3.26.2, “Input impedance and ADC accuracy Table 47 (DSPI characteristics), modified symbol for t_{PCSC} and t_{PASC}
11	14 Nov 2012	In the cover feature list: added “and ECC” at the end of “Up to 512 KB on-chip code flash supported with the flash controller” added “with ECC” at the end of “Up to 48 KB on-chip SRAM” Table 13 (Recommended operating conditions (3.3 V)), removed minimum value of T_{VDD} and relative footnote. Table 14 (Recommended operating conditions (5.0 V)), removed minimum value of T_{VDD} and relative footnote.